

Contents

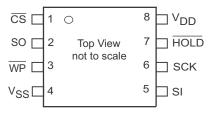
Pinouts	3
Pin Definitions	3
Overview	4
Memory Architecture	4
Serial Peripheral Interface – SPI Bus	4
SPI Overview	4
SPI Modes	
Power Up to First Access	6
Command Structure	6
WREN - Set Write Enable Latch	6
WRDI - Reset Write Enable Latch	
Status Register and Write Protection	6
RDSR - Read Status Register	7
WRSR - Write Status Register	7
Memory Operation	
Write Operation	8
Read Operation	8
HOLD Pin Operation	9
Endurance	
Maximum Ratings	11
Operating Range	11

DC Electrical Characteristics	11
Data Retention and Endurance	12
Capacitance	12
Thermal Resistance	12
AC Test Conditions	12
AC Switching Characteristics	13
Power Cycle Timing	15
Ordering Information	
Ordering Code Definitions	
Package Diagram	
Acronyms	
Document Conventions	
Units of Measure	
Document History Page	
Sales, Solutions, and Legal Information	
Worldwide Sales and Design Support	
Products	
PSoC® Solutions	20
Cypress Developer Community	20
Technical Support	
••	



Pinouts

Figure 1. 8-pin SOIC pinout



Pin Definitions

Pin Name	I/O Type	Description
CS	Input	Chip Select . This active LOW input activates the device. When HIGH, the device enters low-power standby mode, ignores other inputs, and tristates the output. When LOW, the device internally activates the SCK signal. A falling edge on CS must occur before every opcode.
SCK	Input	Serial Clock. All I/O activity is synchronized to the serial clock. Inputs are latched on the rising edge and outputs occur on the falling edge. Because the device is synchronous, the clock frequency may be any value between 0 and 20 MHz and may be interrupted at any time.
SI ^[1]	Input	Serial Input . All data is input to the device on this pin. The pin is sampled on the rising edge of SCK and is ignored at other times. It should always be driven to a valid logic level to meet I_{DD} specifications.
SO ^[1]	Output	Serial Output. This is the data output pin. It is driven during a read and remains tristated at all other times including when HOLD is LOW. Data transitions are driven on the falling edge of the serial clock.
WP	Input	Write Protect. This active LOW pin prevents all write operation, including Status Register. If HIGH, write access is determined by the other write protection features, as controlled through the Status Register. A complete explanation of write protection is provided in Status Register and Write Protection on page 7. This pin must be tied to V_{DD} if not used.
HOLD	Input	HOLD Pin . The HOLD pin is used when the host CPU must interrupt a memory operation for another task. When HOLD is LOW, the current operation is suspended. The device ignores any transition on SCK or CS. All transitions on HOLD must occur while SCK is LOW. This pin must be tied to V_{DD} if not used.
V _{SS}	Power supply	Ground for the device. Must be connected to the ground of the system.
V _{DD}	Power supply	Power supply input to the device.

Note

1. SI may be connected to SO for a single pin data interface.



Overview

The FM25040B is a serial F-RAM memory. The memory array is logically organized as 512 \times 8 bits and is accessed using an industry standard serial peripheral interface (SPI) bus. The functional operation of the F-RAM is similar to serial flash and serial EEPROMs. The major difference between the FM25040B and a serial flash or EEPROM with the same pinout is the F-RAM's superior write performance, high endurance, and low power consumption.

Memory Architecture

When accessing the FM25040B, the user addresses 512 locations of eight data bits each. These eight data bits are shifted in or out serially. The addresses are accessed using the SPI protocol, which includes a chip select (to permit multiple devices on the bus), an opcode including the upper address bit, and a word address. The word address consist of the lower 8-address bits. The complete address of 9 bits specifies each byte address uniquely.

Most functions of the FM25040B are either controlled by the SPI interface or handled by on-board circuitry. The access time for the memory operation is essentially zero, beyond the time needed for the serial protocol. That is, the memory is read or written at the speed of the SPI bus. Unlike a serial flash or EEPROM, it is not necessary to poll the device for a ready condition because writes occur at bus speed. By the time a new bus transaction can be shifted into the device, a write operation is complete. This is explained in more detail in the interface section.

Note The FM25040B contains no power management circuits other than a simple internal power-on reset circuit. It is the user's responsibility to ensure that V_{DD} is within datasheet tolerances to prevent incorrect operation. It is recommended that the part is not powered down with chip enable active.

Serial Peripheral Interface – SPI Bus

The FM25040B is a SPI slave device and operates at speeds up to 20 MHz. This high-speed serial bus provides high-performance serial communication to a SPI master. Many common microcontrollers have hardware SPI ports allowing a direct interface. It is quite simple to emulate the port using ordinary port pins for microcontrollers that do not. The FM25040B operates in SPI Mode 0 and 3.

SPI Overview

The SPI is a four-pin interface with Chip Select (\overline{CS}), Serial Input (SI), Serial Output (SO), and Serial Clock (SCK) pins.

The SPI is a synchronous serial interface, which uses clock and data pins for memory access and supports multiple devices on the data bus. A device on the SPI bus is activated using the \overline{CS} pin.

The relationship between chip select, clock, and data is dictated by the SPI mode. This device supports SPI modes 0 and 3. In The SPI protocol is controlled by opcodes. These opcodes specify the commands from the bus master to the slave device. After \overline{CS} is activated, the first byte transferred from the bus master is the opcode. Following the opcode, any addresses and data are then transferred. The \overline{CS} must go inactive after an operation is complete and before a new opcode can be issued. The commonly used terms in the SPI protocol are as follows:

SPI Master

The SPI master device controls the operations on a SPI bus. An SPI bus may have only one master with one or more slave devices. All the slaves share the same SPI bus lines and the master may select any of the slave devices using the \overline{CS} pin. All of the operations must be initiated by the master activating a slave device by pulling the \overline{CS} pin of the slave LOW. The master also generates the SCK and all the data transmission on SI and SO lines are synchronized with this clock.

SPI Slave

The SPI slave device is activated by the master through the Chip Select line. A slave device gets the SCK as an input from the SPI master and all the communication is synchronized with this clock. An SPI slave never initiates a communication on the SPI bus and acts only on the instruction from the master.

The FM25040B operates as an SPI slave and may share the SPI bus with other SPI slave devices.

Chip Select (CS)

To select any slave device, the master needs to pull down the corresponding \overline{CS} pin. Any instruction can be issued to a slave device only while the \overline{CS} pin is LOW. When the device is not selected, data through the SI pin is ignored and the serial output pin (SO) remains in a high-impedance state.

Note A new instruction must begin with the falling edge of \overline{CS} . Therefore, only one opcode can be issued for each active Chip Select cycle.

Serial Clock (SCK)

The Serial Clock is generated by the SPI master and the communication is synchronized with this clock after \overline{CS} goes LOW.

The FM25040B enables SPI modes 0 and 3 for data communication. In both of these modes, the inputs are latched by the slave device on the rising edge of SCK and outputs are issued on the falling edge. Therefore, the first rising edge of SCK signifies the arrival of the first bit (MSB) of a SPI instruction on the SI pin. Further, all data inputs and outputs are synchronized with SCK.

Data Transmission (SI/SO)

The SPI data bus consists of two lines, SI and SO, for serial data communication. SI is also referred to as Master Out Slave In (MOSI) and SO is referred to as Master In Slave Out (MISO). The



master issues instructions to the slave through the SI pin, while the slave responds through the SO pin. Multiple slave devices may share the SI and SO lines as described earlier.

The FM25040B has two separate pins for SI and SO, which can be connected with the master as shown in Figure 2.

For a microcontroller that has no dedicated SPI bus, a general-purpose port may be used. To reduce hardware resources on the controller, it is possible to connect the two data pins (SI, SO) together and tie off (HIGH) the HOLD and WP pins. Figure 3 shows such a configuration, which uses only three pins.

Most Significant Bit (MSB)

The SPI protocol requires that the first bit to be transmitted is the Most Significant Bit (MSB). This is valid for both address and data transmission.

The 4-Kbit serial F-RAM requires an opcode including the upper address bit, and a word address for any read or write operation.

The word address consist of the lower 8-address bits. The complete address of 9 bits specifies each byte address uniquely.

Serial Opcode

After the slave device is selected with \overline{CS} going LOW, the first byte received is treated as the opcode for the intended operation. FM25040B uses the standard opcodes for memory accesses.

Invalid Opcode

If an invalid opcode is received, the opcode is ignored and the device ignores any <u>additional</u> serial data on the SI pin until the next falling edge of CS, and the SO pin remains tristated.

Status Register

FM25040B has an 8-bit Status Register. The bits in the Status Register are used to configure the device. These bits are described in Table 3 on page 7.

Figure 2. System Configuration with SPI port

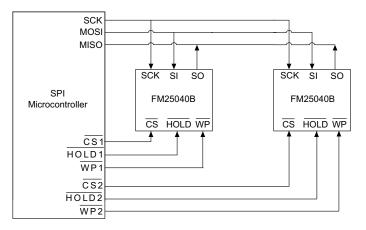
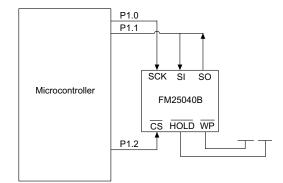


Figure 3. System Configuration without SPI port



SPI Modes

FM25040B may be driven by a microcontroller with its SPI peripheral running in either of the following two modes:

- SPI Mode 0 (CPOL = 0, CPHA = 0)
- SPI Mode 3 (CPOL = 1, CPHA = 1)

For both these modes, the input data is latched in on the rising edge of SCK starting from the first rising edge after \overline{CS} goes active. If the clock starts from a HIGH state (in mode 3), the first rising edge after the clock toggles is considered. The output data is available on the falling edge of SCK.

Document Number: 001-86145 Rev. *G



The two SPI modes are shown in Figure 4 on page 6 and Figure 5 on page 6. The status of the clock when the bus master is not transferring data is:

- SCK remains at 0 for Mode 0
- SCK remains at 1 for Mode 3

The device detects the SPI mode from the status of the SCK pin when the device is selected by bringing the \overline{CS} pin LOW. If the SCK pin is LOW when the device is selected, SPI Mode 0 is assumed and if the SCK pin is HIGH, it works in SPI Mode 3.

Figure 4. SPI Mode 0

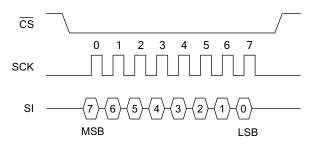
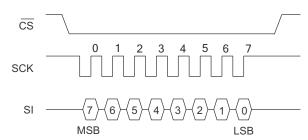


Figure 5. SPI Mode 3



Power Up to First Access

The FM25040B is not accessible for a t_{PU} time after power up. Users must comply with the timing parameter t_{PU} , which is the minimum time from V_{DD} (min) to the first \overline{CS} LOW.

Command Structure

There are six commands, called opcodes, that can be issued by the bus master to the FM25040B. They are listed in Table 1. These opcodes control the functions performed by the memory.

Table	1.	Opcode comn	nands
-------	----	-------------	-------

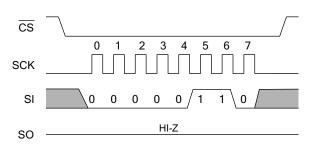
Name	Description	Opcode
WREN	Set write enable latch	0000 0110b
WRDI	Write disable	0000 0100b
RDSR	Read Status Register	0000 0101b
WRSR	Write Status Register	0000 0001b
READ	Read memory data	0000 A011b
WRITE	Write memory data	0000 A010b

WREN - Set Write Enable Latch

The FM25040B will power up with writes disabled. The WREN command must be issued before any write operation. Sending the WREN opcode allows the user to issue subsequent opcodes for write operations. These include writing the Status Register (WRSR) and writing the memory (WRITE).

Sending the WREN opcode causes the internal Write Enable Latch to be set. A flag bit in the Status Register, called WEL, indicates the state of the latch. WEL = '1' indicates that writes are permitted. Attempting to write the WEL bit in the Status Register has no effect on the state of this bit – only the WREN opcode can set this bit. The WEL bit will be automatically cleared on the rising edge of \overline{CS} following a WRDI, a WRSR, or a WRITE operation. This prevents further writes to the Status Register or the F-RAM array without another WREN command. Figure 6 illustrates the WREN command bus configuration.

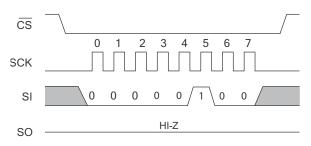
Figure 6. WREN Bus Configuration



WRDI - Reset Write Enable Latch

The WRDI command disables all write activity by clearing the Write Enable Latch. The user can verify that writes are disabled by reading the WEL bit in the Status Register and verifying that WEL is equal to '0'. Figure 7 illustrates the WRDI command bus configuration.

Figure 7. WRDI Bus Configuration





Status Register and Write Protection

The write protection features of the FM25040B are multi-tiered and are enabled through the status register. First, a WREN opcode must be issued prior to any write operation. Assuming that writes are enabled using WREN, writes to memory are controlled by the WP pin and the Status Register. When WP is LOW, the entire part is write-protected. When \overline{WP} is HIGH, the memory protection is subject to the Status Register. Writes to the Status Register are performed using the WREN and WRSR commands and subject to the \overline{WP} pin. The Status Register is organized as follows. (The default value shipped from the factory for bits in the Status Register is '0'.)

Table 2. Status Register

Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
X (0)	X (0)	X (0)	X (0)	BP1 (0)	BP0 (0)	WEL (0)	X (0)

Table 3. Status Register Bit Definition

Bit	Definition	Description	
Bit 0	Don't care	This bit is non-writable and always returns '0' upon read.	
Bit 1 (WEL)	Write Enable Latch	WEL indicates if the device is write enabled. This bit defaults to '0' (disabled) on power-up. WEL = '1'> Write enabled WEL = '0'> Write disabled	
Bit 2 (BP0)	Block Protect bit '0'	sed for block protection. For details, see Table 4 on page 7.	
Bit 3 (BP1)	Block Protect bit '1'	Used for block protection. For details, see Table 4 on page 7.	
Bit 4-7	Don't care	These bits are non-writable and always return '0' upon read.	

Bits 0 and 4-7 are fixed at '0'; none of these bits can be modified. Note that bit 0 ("Ready or Write in progress" bit in serial flash and EEPROM) is unnecessary, as the F-RAM writes in real-time and is never busy, so it reads out as a '0'. The BP1 and BP0 control the software write-protection features and are nonvolatile bits. The WEL flag indicates the state of the Write Enable Latch. Attempting to directly write the WEL bit in the Status Register has no effect on its state. This bit is internally set and cleared via the WREN and WRDI commands, respectively.

BP1 and BP0 are memory block write protection bits. They specify portions of memory that are write-protected as shown in Table 4.

Table 4. Block Memory Write Protection

BP1	BP0	Protected Address Range	
0	0	None	
0	1	180h to 1FFh (upper 1/4)	
1	0	100h to 1FFh (upper 1/2)	
1	1	000h to 1FFh (all)	

The BP1 and BP0 bits and the Write Enable Latch are the only mechanisms that protect the memory from writes. The remaining write protection features protect inadvertent changes to the block protect bits.

The BP1 and BP0 bits allow software to selectively write protect the array. These settings are only used when the WP pin is inactive and the WREN command has been issued. Table 5 summarizes the write protection conditions.

Table 5. Write Protection

WEL	WP	Protected Blocks	Unprotected Blocks	Status Register
0	Х	Protected	Protected	Protected
1	0	Protected	Protected	Protected
1	1	Protected	Unprotected	Unprotected

RDSR - Read Status Register

The RDSR command allows the bus master to verify the contents of the Status Register. Reading the status register provides information about the current state of the write-protection features. Following the RDSR opcode, the FM25040B will return one byte with the contents of the Status Register.

WRSR - Write Status Register

The WRSR command allows the SPI bus master to write into the Status Register and change the write protect configuration by setting the BP0 and <u>BP1</u> bits as required. Before issuing a WRSR command, the <u>WP pin</u> must be HIGH or inactive. Note that on the FM25040B, WP prevents writing to the Status Register and the memory array. Before sending the WRSR command, the user must send a WREN command to enable writes. Executing a WRSR command is a write operation and therefore, clears the Write Enable Latch.



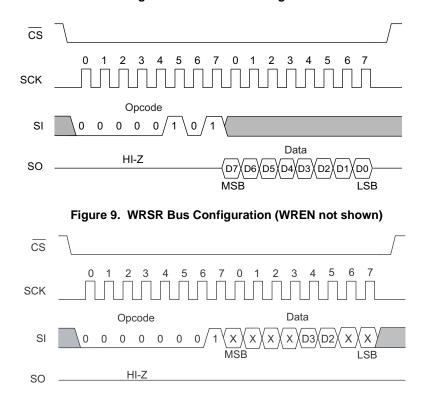


Figure 8. RDSR Bus Configuration

Memory Operation

The SPI interface, which is capable of a high clock frequency, highlights the fast write capability of the F-RAM technology. Unlike serial flash and EEPROMs, the FM25040B can perform sequential writes at bus speed. No page register is needed and any number of sequential writes may be performed.

Write Operation

All writes to the memory begin with a WREN opcode. The WRITE opcode includes the upper bit of the memory address. Bit 3 in the opcode corresponds to the upper address bit (A8). The next byte is the lower 8-bits of the address (A7-A0). In total, the 9-bits specify the address of the first byte of the write operation. Subsequent bytes are data bytes, which are written sequentially. Addresses are incremented internally as long as the bus master continues to issue clocks and keeps CS LOW. If the last address of 1FFh is reached, the counter will roll over to 000h. Data is written MSB first. The rising edge of CS terminates a write operation. A write operation is shown in Figure 10.

Note When a burst write reaches a protected block address, the automatic address increment stops and all the subsequent data bytes received for write will be ignored by the device.

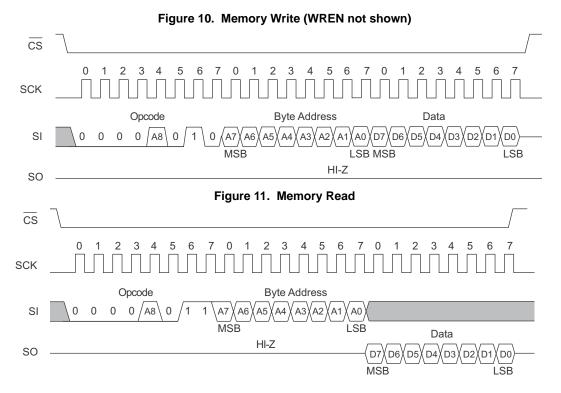
EEPROMs use page buffers to increase their write throughput. This compensates for the technology's inherently slow write operations. F-RAM memories do not have page buffers because each byte is written to the F-RAM array immediately after it is clocked in (after the eighth clock). This allows any number of bytes to be written without page buffer delays.

Note If the power is lost in the middle of the write operation, only the last completed byte will be written.

Read Operation

After the falling edge of \overline{CS} , the bus master can issue a READ opcode. The READ opcode includes the upper bit of the memory address. Bit 3 in the opcode corresponds to the upper address bit (A8). The next byte is the lower 8-bits of the address (A7-A0). In total, the 9-bits specify the address of the first byte of the read operation. After the opcode and address are issued, the device drives out the read data on the next eight clocks. The SI input is ignored during read data bytes. Subsequent bytes are data bytes, which are read out sequentially. Addresses are incremented internally as long as the bus master continues to issue clocks and \overline{CS} is LOW. If the last address of 1FFh is reached, the counter will roll over to 000h. Data is read MSB first. The rising edge of \overline{CS} terminates a read operation and tristates the SO pin. A read operation is shown in Figure 11.

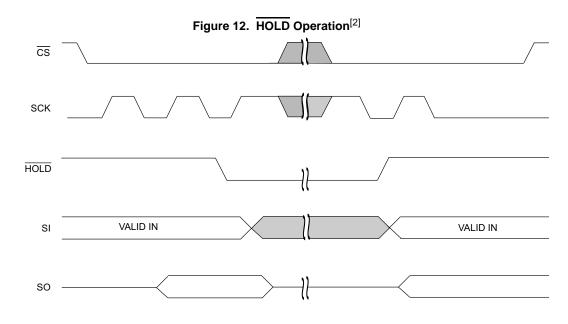




HOLD Pin Operation

The HOLD pin can be used to interrupt a serial operation without aborting it. If the bus master pulls the HOLD pin LOW while SCK is LOW, the current operation will pause. Taking the HOLD pin

HIGH while <u>SCK</u> is LOW will resume an operation. The transitions of HOLD must occur while SCK is LOW, but the SCK and \overline{CS} can toggle during a hold state.



Note

2. Figure shows HOLD operation for input mode and output mode.

Document Number: 001-86145 Rev. *G



Endurance

The FM25040B devices are capable of being accessed at least 10¹⁴ times, reads or writes. An F-RAM memory operates with a read and restore mechanism. Therefore, an endurance cycle is applied on a row basis for each access (read or write) to the memory array. The F-RAM architecture is based on an array of rows and columns of 64 rows of 64-bits each. The entire row is internally accessed once whether a single byte or all eight bytes are read or written. Each byte in the row is counted only once in an endurance calculation. Table 6 shows endurance calculations for a 64-byte repeating loop, which includes an opcode, a starting address, and a sequential 64-byte data stream. This causes each byte to experience one endurance cycle through the loop.

F-RAM read and write endurance is virtually unlimited even at a 20 MHz clock rate.

Table 6. Time to Reach Endurance Limit for Repeating64-byte Loop

SCK Freq (MHz)	Endurance Cycles/sec	Endurance Cycles/year	Years to Reach Limit
20	37,310	1.18 × 10 ¹²	85.1
10	18,660	5.88 × 10 ¹¹	170.2
5	9,330	2.94 × 10 ¹¹	340.3



Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. These user guidelines are not tested.

Storage temperature55 °C to +125 °C
Maximum accumulated storage time At 125 °C ambient temperature 1000 h At 85 °C ambient temperature
Ambient temperature with power applied55 °C to +125 °C
Supply voltage on V _{DD} relative to V _{SS} 1.0 V to +7.0 V
Input voltage1.0 V to +7.0 V and V _{IN} < V _{DD} +1.0 V
DC voltage applied to outputs in High Z state0.5 V to V_{DD} + 0.5 V
Transient voltage (< 20 ns) on any pin to ground potential–2.0 V to V_{DD} + 2.0 V

Package power dissipation capability (T_A = 25 °C) 1.0 W Surface mount lead soldering temperature (3 seconds)+260 °C DC output current (1 output at a time, 1s duration) 15 mA Electrostatic Discharge Voltage Human Body Model (AEC-Q100-002 Rev. E) 3.5 kV Charged Device Model (AEC-Q100-011 Rev. B) 1.25 kV Latch up current> 140 mA

Operating Range

Range	Ambient Temperature (T _A)	V _{DD}
Industrial	–40 °C to +85 °C	4.5 V to 5.5 V

DC Electrical Characteristics

Over the Operating Range

Parameter	Description	Test Conditions		Min	Typ ^[3]	Max	Unit
V _{DD}	Power supply			4.5	5.0	5.5	V
I _{DD}	V _{DD} supply current	SCK toggling between	f _{SCK} = 1 MHz	_	Ι	0.25	mA
		$V_{DD} - 0.3$ V and V_{SS} , other inputs V_{SS} or $V_{DD} - 0.3$ V. SO = Open.	f _{SCK} = 20 MHz	_	-	4	mA
I _{SB}	V _{DD} standby current	CS = V _{DD} . All other inpu	uts V _{SS} or V _{DD} .	_	4	10	μA
I _{LI}	Input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$		-	-	±1	μΑ
I _{LO}	Output leakage current	$V_{SS} \le V_{OUT} \le V_{DD}$		-	-	±1	μA
V _{IH}	Input HIGH voltage			$0.7 \times V_{DD}$	Ι	V _{DD} + 0.3	V
V _{IL}	Input LOW voltage			- 0.3	Ι	$0.3 \times V_{DD}$	V
V _{OH}	Output HIGH voltage	I _{OH} = -2 mA		V _{DD} – 0.8	-	_	V
V _{OL}	Output LOW voltage	I _{OL} = 2 mA		—	—	0.4	V
V _{HYS} ^[4]	Input Hysteresis (CS and SCK pin)			$0.05 \times V_{DD}$	-	_	V

Notes

Typical values are at 25 °C, V_{DD} = V_{DD}(typ). Not 100% tested.
 This parameter is characterized but not 100% tested.



Data Retention and Endurance

Parameter	Description	Test condition	Min	Max	Unit
T _{DR}	Data retention	T _A = 85 °C	10	_	Years
		T _A = 75 °C	38	_	
		$T_A = 65 \ ^{\circ}C$	151	_	
NV _C	Endurance	Over operating temperature	10 ¹⁴	_	Cycles

Capacitance

Parameter ^[5]	Description	Test Conditions	Max	Unit
C _O	Output pin capacitance (SO)	$T_A = 25 \text{ °C}, f = 1 \text{ MHz}, V_{DD} = V_{DD}(typ)$	8	pF
Cl	Input pin capacitance		6	pF

Thermal Resistance

Parameter	Description	Test Conditions	8-pin SOIC	Unit
Θ_{JA}	Thermal resistance (junction to ambient)	Test conditions follow standard test methods and procedures for measuring thermal impedance, per EIA /	148	°C/W
Θ_{JC}	Thermal resistance (junction to case)	JESD51.	48	°C/W

AC Test Conditions

Input pulse levels	10% and 90% of $V_{\mbox{\scriptsize DD}}$
Input rise and fall times	5 ns
Input and output timing reference	ce levels0.5 × V_{DD}
Output load capacitance	

Note 5. This parameter is characterized but not 100% tested.



AC Switching Characteristics

Over the Operating Range

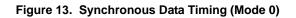
Parameters ^[6]					
Cypress Parameter	Alt. Parameter	Description		Мах	Unit
f _{SCK}	—	SCK Clock frequency	0	20	MHz
t _{CH}	_	Clock HIGH time	22	Ι	ns
t _{CL}	-	Clock LOW time	22	-	ns
t _{CSU}	t _{CSS}	Chip select setup	10	-	ns
t _{CSH}	t _{CSH}	Chip select hold	10	-	ns
t _{OD} ^[7, 8, 9]	t _{HZCS}	Output disable time	-	20	ns
t _{ODV}	t _{CO}	Output data valid time	_	20	ns
t _{OH}	-	Output hold time	0	-	ns
t _D	-	Deselect time	60	-	ns
t _R ^[10, 11]	-	Data in rise time	-	50	ns
t _F ^[10, 11]	-	Data in fall time	-	50	ns
t _{SU}	t _{SD}	Data setup time	5	_	ns
t _H	t _{HD}	Data hold time	5	_	ns
t _{HS}	t _{SH}	HOLD setup time	10	_	ns
t _{HH}	t _{HH}	HOLD hold time	10	_	ns
t _{HZ} [7, 8]	t _{HHZ}	HOLD LOW to HI-Z	_	20	ns
t _{LZ} ^[8]	t _{HLZ}	HOLD HIGH to data active	_	20	ns

Notes

- 7. t_{OD} and t_{HZ} are specified with a load capacitance of 5 pF. Transition is measured when the outputs enter a high impedance state.
- 8. This parameter is characterized but not 100% tested.
- 9. For clock high time $t_{CH} \le 35$ ns, the parameter t_{ODV} is extended such that $t_{CH} + t_{ODV} \le 65$ ns.
- 10. Rise and fall times measured between 10% and 90% of waveform.
- 11. These parameters are guaranteed by design and are not tested.

^{6.} Test conditions assume a signal transition time of 5 ns or less, timing reference levels of 0.5 × V_{DD} , input pulse levels of 10% to 90% of V_{DD} , and output loading of the specified I_{OL}/I_{OH} and 30 pF load capacitance shown in AC Test Conditions on page 12.





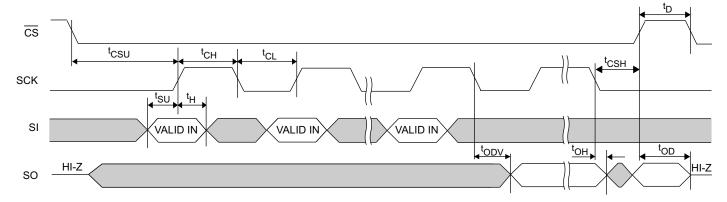
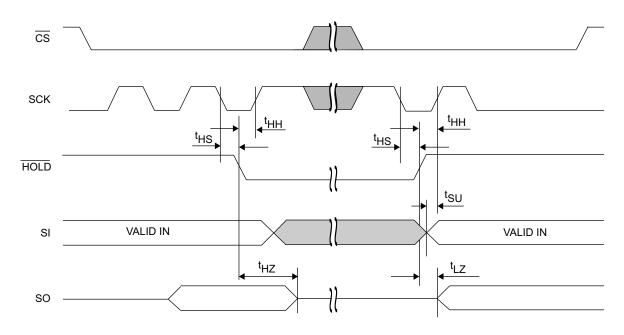


Figure 14. HOLD Timing



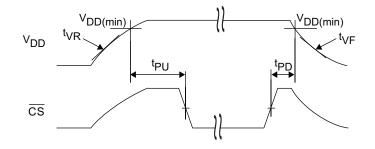


Power Cycle Timing

Over the Operating Range

Parameter	Description	Min	Max	Unit
t _{PU}	Power-up V _{DD} (min) to first access (CS LOW)	1	-	ms
t _{PD}	Last access (CS HIGH) to power-down (V _{DD} (min))		_	μs
t _{VR} ^[12]	V _{DD} power-up ramp rate	30	-	µs/V
t _{VF} ^[12]	V _{DD} power-down ramp rate	30	_	µs/V

Figure 15. Power Cycle Timing



Note 12. Slope measured at any point on V_{DD} waveform.

Document Number: 001-86145 Rev. *G

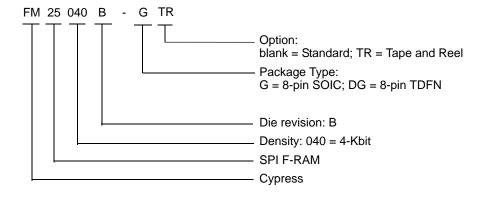


Ordering Information

Ordering Code	Package Diagram	Package Type	Operating Range
FM25040B-G	51-85066	8-pin SOIC	Industrial
FM25040B-GTR	51-85066	8-pin SOIC	

All these parts are Pb-free. Contact your local Cypress sales representative for availability of these parts.

Ordering Code Definitions



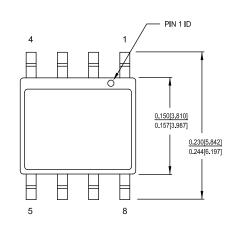


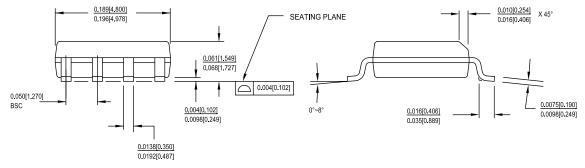
Package Diagram

Figure 16. 8-pin SOIC (150 Mils) Package Outline, 51-85066

- 1. DIMENSIONS IN INCHES[MM] MIN. MAX.
- 2. PIN 1 ID IS OPTIONAL, ROUND ON SINGLE LEADFRAME RECTANGULAR ON MATRIX LEADFRAME
- 3. REFERENCE JEDEC MS-012
- 4. PACKAGE WEIGHT 0.07gms

PART #				
S08.15	STANDARD PKG			
SZ08.15	LEAD FREE PKG			
SW8.15	LEAD FREE PKG			





51-85066 *G



Acronyms

Acronym	Description
AEC	Automotive Electronics Council
CPHA	Clock Phase
CPOL	Clock Polarity
EEPROM	Electrically Erasable Programmable Read-Only Memory
EIA	Electronic Industries Alliance
I/O	Input/Output
JEDEC	Joint Electron Devices Engineering Council
JESD	JEDEC Standards
LSB	Least Significant Bit
MSB	Most Significant Bit
F-RAM	Ferroelectric Random Access Memory
RoHS	Restriction of Hazardous Substances
SPI	Serial Peripheral Interface
SOIC	Small Outline Integrated Circuit

Document Conventions

Units of Measure

Symbol	Unit of Measure
°C	degree Celsius
Hz	hertz
kHz	kilohertz
KΩ	kilohm
Kbit	kilobit
kV	kilovolt
MHz	megahertz
μA	microampere
μs	microsecond
mA	milliampere
ms	millisecond
ns	nanosecond
Ω	ohm
%	percent
pF	picofarad
V	volt
W	watt



Document History Page

Docume	nt Title: FM25040B,	4-Kbit (512	× 8) Serial (SPI) F-RAM
	nt Number 001 001			

Rev.	ECN No.	Orig. of Change	Submission Date	Description of Change
**	3902952	GVCH	02/25/2013	New spec
*A	3924523	GVCH	03/07/2013	Changed minimum value of t _{PU} parameter from 10 ms to 1 ms.
*В	3994285	GVCH	05/14/2013	Added Appendix A - Errata for FM25040B
*C	4045438	GVCH	06/30/2013	All errata items are fixed and the errata is removed.
*D	4226124	GVCH	01/24/2014	Converted to Cypress standard format Updated Maximum Ratings table - Removed Moisture Sensitivity Level (MSL) - Added junction temperature and latch up current Updated Data Retention and Endurance table - Added data retention value at 65 °C and 75 °C temperature Added Thermal Resistance table Removed Package Marking Scheme (top mark) Removed Ramtron revision history Completing Sunset Review
*E	4306361	GVCH	03/12/2014	Typo fixed (Document History Page): Document number corrected from 001-86146 to 001-86145.
*F	4564960	GVCH	11/10/2014	Added related documentation hyperlink in page 1.
*G	4878519	ZSK / PSR	08/10/2015	Updated Maximum Ratings: Removed "Maximum junction temperature". Added "Maximum accumulated storage time". Added "Ambient temperature with power applied". Updated Package Diagram: spec 51-85066 – Changed revision from *F to *G. Updated to new template.



Sales, Solutions, and Legal Information

Worldwide Sales and Design Support

Cypress maintains a worldwide network of offices, solution centers, manufacturer's representatives, and distributors. To find the office closest to you, visit us at Cypress Locations.

Products

Automotive	cypress.com/go/automotive
Clocks & Buffers	cypress.com/go/clocks
Interface	cypress.com/go/interface
Lighting & Power Control	cypress.com/go/powerpsoc
Memory	cypress.com/go/memory
PSoC	cypress.com/go/psoc
Touch Sensing	cypress.com/go/touch
USB Controllers	cypress.com/go/USB
Wireless/RF	cypress.com/go/wireless

PSoC[®] Solutions

psoc.cypress.com/solutions PSoC 1 | PSoC 3 | PSoC 4 | PSoC 5LP

Cypress Developer Community Community | Forums | Blogs | Video | Training

Technical Support cypress.com/go/support

© Cypress Semiconductor Corporation, 2013-2015. The information contained herein is subject to change without notice. Cypress Semiconductor Corporation assumes no responsibility for the use of any circuitry other than circuitry embodied in a Cypress product. Nor does it convey or imply any license under patent or other rights. Cypress products are not warranted nor intended to be used for medical, life support, life saving, critical control or safety applications, unless pursuant to an express written agreement with Cypress. Furthermore, Cypress does not authorize its products for use as critical components in life-support systems where a malfunction or failure may reasonably be expected to result in significant injury to the user. The inclusion of Cypress products in life-support systems application implies that the manufacturer assumes all risk of such use and in doing so indemnifies Cypress against all charges.

Any Source Code (software and/or firmware) is owned by Cypress Semiconductor Corporation (Cypress) and is protected by and subject to worldwide patent protection (United States and foreign), United States copyright laws and international treaty provisions. Cypress hereby grants to licensee a personal, non-exclusive, non-transferable license to copy, use, modify, create derivative works of, and compile the Cypress Source Code and derivative works for the sole purpose of creating custom software and or firmware in support of licensee product to be used only in conjunction with a Cypress integrated circuit as specified in the applicable agreement. Any reproduction, modification, translation, compilation, or representation of this Source Code except as specified above is prohibited without the express written permission of Cypress.

Disclaimer: CYPRESS MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARD TO THIS MATERIAL, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE. Cypress reserves the right to make changes without further notice to the materials described herein. Cypress does not assume any liability arising out of the application or use of any product or circuit described herein. Cypress does not authorize its products for use as critical components in life-support systems where a malfunction or failure may reasonably be expected to result in significant injury to the user. The inclusion of Cypress' product in a life-support systems application implies that the manufacturer assumes all risk of such use and in doing so indemnifies Cypress against all charges.

Use may be limited by and subject to the applicable Cypress software license agreement.

Document Number: 001-86145 Rev. *G

Revised August 10, 2015

Page 20 of 20

All products and company names mentioned in this document may be the trademarks of their respective holders.